

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: Naoya SASHIDA et al.

Serial Number: 09/321,605

Filed: May 28, 1999

For: METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE HAVING CAPACITOR (as amended)



Group Art Unit: 2813

Examiner: Chen, J.

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-Step 2
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RESPONSE UNDER 37 C.F.R. §116
-EXPEDITED RESPONSE-
GROUP ART UNIT 2813

BOX AF

Director of Patents and Trademarks
Washington, D.C. 20231

January 16, 2001

Dear Sir:

(1/29/01) In response to the Office Action dated September 14, 2000, please reconsider the above-identified application amended as follows:

IN THE CLAIMS:

Please amend claims 1, 2 and 21 as follows:

- (B)*
1. (Amended) A method of manufacturing a semiconductor device comprising the steps of:
- forming an impurity diffusion layer in a semiconductor substrate;
- forming a first insulating film covering the semiconductor substrate;

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